

Version with Markings to Show Changes Made

Claim 1 is amended as follows:

1. (amended) A method for fabricating a BiCMOS integrated circuit, comprising the steps of:

forming in a single implantation step a base region of a bipolar transistor and a p-well of an n-channel MOS transistor; and

forming in a single implantation step a collector contact well of a bipolar transistor and an n-well of a p-channel MOS transistor, said collector contact well adjoining a collector region and extending to a surface of a semiconductor substrate.